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JH. Wei[1], W. Mao[1], H. Fang[2], Z. Zhang[2], JX. Zhang[2], BJ. La[n2] and J. Wan[1]
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Haiying Yuan, Kai Zhang, Tong Zheng and Yichen Wang
Faculty of Information Technology, Beijing University of Technology, Beijing, China

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Chang Liu, Kai Wang, Mingcheng Luo, Yaozu Guo, Feng Yan and Xiaoli Ji
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